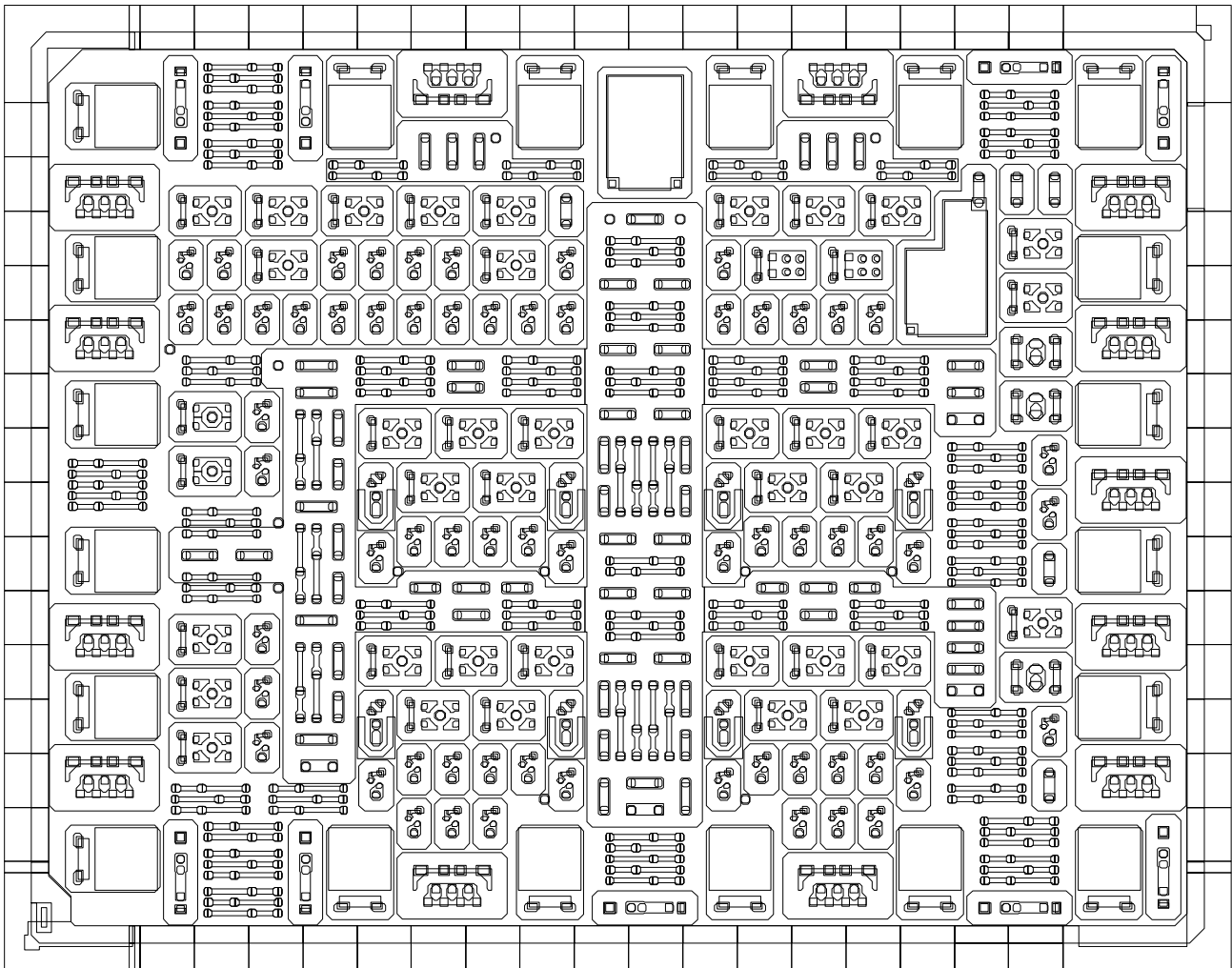


- Special Features:**
- improved V_{BE} -matching
 - Trimmcells
 - SiCr Resistors
 - 40V-NPN-Transistors
 - low leakage PNP-Transistors

Die Size	app. 2.5 x 2.0 mm ²	1.2 k Ω Resistor (base diffused)	14
V_{max}	36 V	0.6 k Ω Resistor (base diffused)	14
Bonding Pads	20	12 k Ω Resistor (SiCr)	124
40 V 40 mA NPN Transistor	13	6 k Ω Resistor (SiCr)	124
20 mA NPN Transistor	2	Crossunder	66
10 mA NPN Transistor	3	18 pF Capacitor	1
5 mA NPN Transistor	70	19 pF Capacitor	1
5 mA NPN Transistor (trimmcell)	9	Total Resistance (diffused)	25 k Ω
1 mA PNP Transistor lateral	36	Total Resistance (SiCr)	2.2 M Ω
1 mA PNP Transistor lateral (low leakage)	2	Total Capacitance	37 pF



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page: 1 of 1C:\Users\Ulberto

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